

**TLP521GB, TLP521-2GB, TLP521-4GB, TLP521, TLP521-2, TLP521-4
TLP521XGB, TLP521-2XGB, TLP521-4XGB
TLP521X, TLP521-2X, TLP521-4X**



**HIGH DENSITY MOUNTING
PHOTOTRANSISTOR
OPTICALLY COUPLED ISOLATORS**

APPROVALS

- UL recognised, File No. E91231

'X' SPECIFICATION APPROVALS

- VDE 0884 in 3 available lead form :-
 - STD
 - G form
 - SMD approved to CECC 00802
- BSI approved - Certificate No. 8001

DESCRIPTION

The TLP521, TLP521-2, TLP521-4 series of optically coupled isolators consist of infrared light emitting diodes and NPN silicon photo transistors in space efficient dual in line plastic packages.

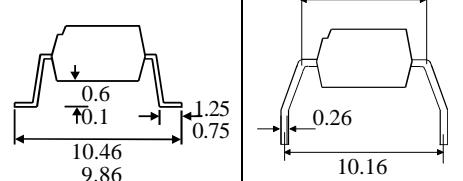
FEATURES

- Options :-
 - 10mm lead spread - add G after part no.
 - Surface mount - add SM after part no.
 - Tape&reel - add SMT&R after part no.
- High Current Transfer Ratio (50% min)
- High Isolation Voltage (5.3kV_{RMS}, 7.5kV_{PK})
- High BV_{CEO} (55Vmin)
- All electrical parameters 100% tested
- Custom electrical selections available

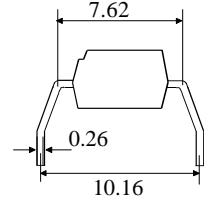
APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances

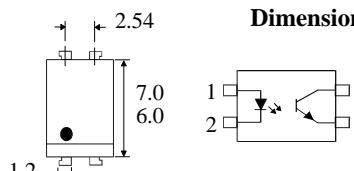
**OPTION SM
SURFACE MOUNT**



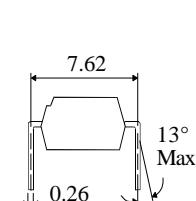
OPTION G



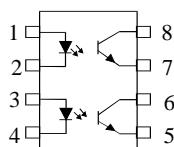
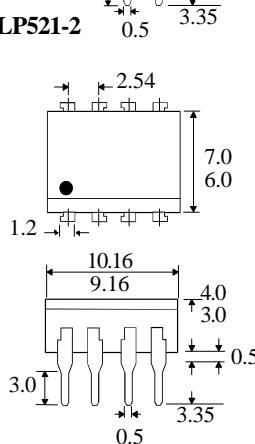
TLP521



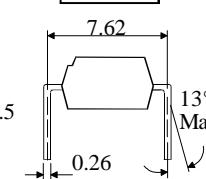
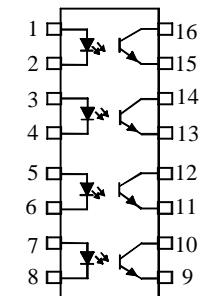
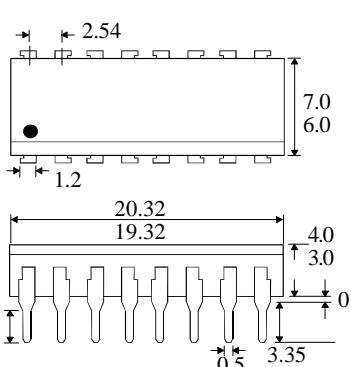
Dimensions in mm



TLP521-2



TLP521-4



13° Max

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ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)

Storage Temperature	—	-55°C to + 125°C
Operating Temperature	—	-30°C to + 100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	—	260°C

INPUT DIODE

Forward Current	—	50mA
Reverse Voltage	—	6V
Power Dissipation	—	70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV _{CEO}	—	55V
Emitter-collector Voltage BV _{ECO}	—	6V
Power Dissipation	—	150mW

POWER DISSIPATION

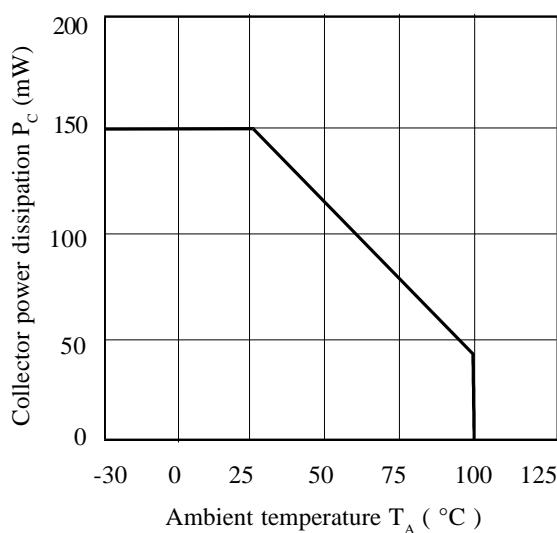
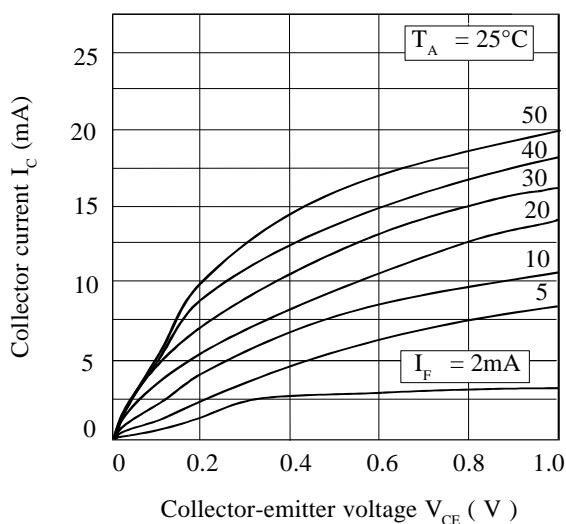
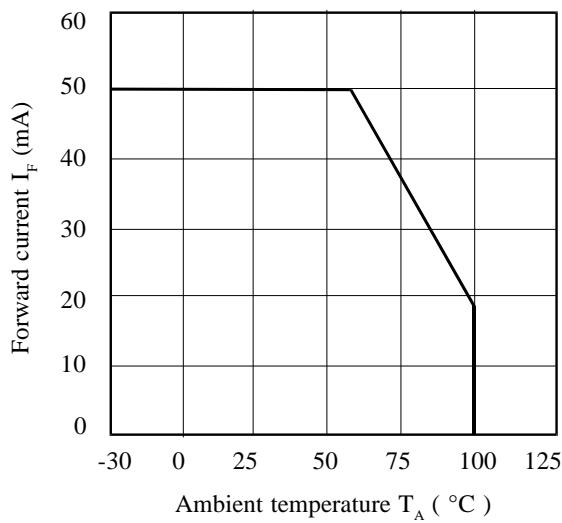
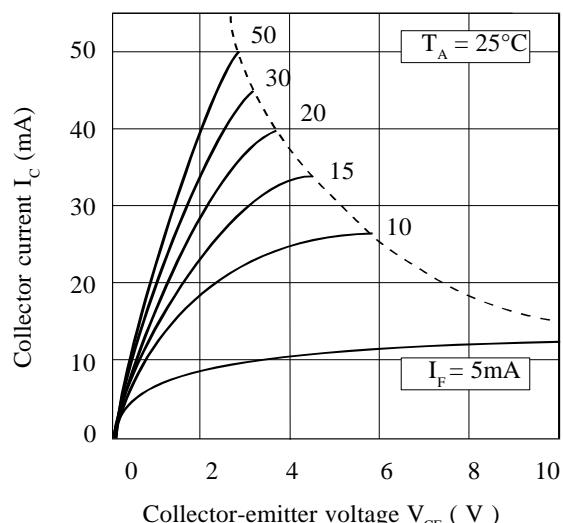
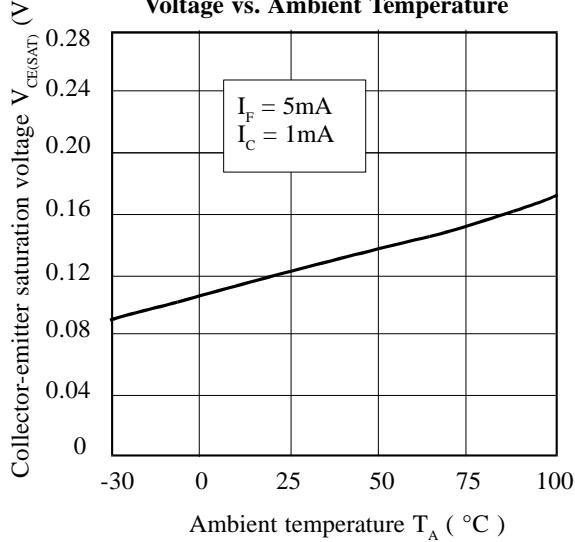
Total Power Dissipation	—	200mW
(derate linearly 2.67mW/°C above 25°C)		

ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V _F)	1.0	1.15	1.3	V	I _F = 10mA
	Reverse Current (I _R)			10	µA	V _R =4V
Output	Collector-emitter Breakdown (BV _{CEO}) (Note 2)	55			V	I _C = 0.5mA
	Emitter-collector Breakdown (BV _{ECO}) Collector-emitter Dark Current (I _{CEO})	6		100	V nA	I _E = 100µA V _{CE} =20V
Coupled	Current Transfer Ratio (CTR) (Note 2) TLP521, TLP521-2, TLP521-4	50		600	%	5mA I _F , 5V V _{CE}
	CTR selection available BL	200		600	%	
	GB	100		600	%	
	GB	30			%	1mA I _F , 0.4V V _{CE}
	Collector-emitter Saturation Voltage V _{CE (SAT)} -GB		0.4	0.4	V V	8mA I _F , 2.4mA I _C 1mA I _F , 0.2mA I _C
	Input to Output Isolation Voltage V _{ISO}	5300			V _{RMS}	See note 1
		7500			V _{PK}	See note 1
	Input-output Isolation Resistance R _{ISO}	5x10 ¹⁰			Ω	V _{IO} =500V (note 1)
	Response Time (Rise), tr		4		µs	V _{CE} =2V,
	Response Time (Fall), tf		3		µs	I _C =2mA, R _L =100Ω

Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

Collector Power Dissipation vs. Ambient Temperature**Collector Current vs. Low Collector-emitter Voltage****Forward Current vs. Ambient Temperature****Collector Current vs. Collector-emitter Voltage****Collector-emitter Saturation Voltage vs. Ambient Temperature****Current Transfer Ratio vs. Forward Current**